¹⁷⁹Pt α decay 1982Bo04,1979Ha10,1970Ha18

History

Type Author Citation Literature Cutoff Date
Full Evaluation M. Shamsuzzoha Basunia NDS 102, 719 (2004) 1-Jun-2004

Parent: 179 Pt: E=0.0; $J^{\pi}=1/2^-$; $T_{1/2}=21.1$ s 4; $Q(\alpha)=5416$ 10; $\%\alpha$ decay=0.24 3

 179 Pt-%α decay: %α=0.24 3, weighted average of %α=0.27 4 (1970Ha18), and %α=0.21 4 (1980Sc09).

Activity produced by protons on U, Th, Au, and Ta; E=5 GeV. Measured Eα. Detector: Surface Barrier Silicon Detector (1982Bo04). Activity produced by protons on Pb; E=600 MeV. Measured Eα, Iα. Detector: Surface Barrier Silicon Detector (1979Ha10,1970Ha18).

¹⁷⁵Os Levels

E(level) J^{π} Comments 102.3 4 $(1/2^{-})$ J^{π} : From Adopted Levels.

α radiations

Additional information 1.

<u>Eα</u> <u>E(level)</u> $Iα^{\frac{\pi}{4}}$ <u>HF</u> 5195 9 102.3 100 $0.91^{\frac{\pi}{1}}$ 13

E α : Weighted average of 5194 *10* (1979Ha10) and 5200 *20* (1970Ha18). Other values: 5150 *10* (1966Si08), 5156 *3* (1982Bo04), 5161 or 5201 (1980Da09). Values of E α given by 1982Bo04 and 1966Si08 do not agree with those given by 1979Ha10 and 1970Ha18. E α data 5150 *10* in 1966Si08 identification based on systematics of (HI,xn γ) excitation functions, T_{1/2}=33 s 2; 5200 *20* in 1970Ha18 from daughter in mass separated source; 5194 *10* in 1979Ha10 from daughter in mass separated Hg source, 5156 *3* in 1982Bo04 using calibration which incorporated the 1966Si08 datum; identified from E α ; T_{1/2}=54 s *4*; and 5161 or 5201 in 1980Da09 identified from E α ; ΔE unstated. However, the adopted T_{1/2}=21.2 s *4* raises doubts about the identity of the α group observed by 1982Bo04 (E α and T_{1/2} are close to values for ¹⁸⁰Pt), and suggests that T_{1/2} from 1966Si08 is also a little high, possibly due to difficulty resolving ¹⁸⁰Pt and ¹⁷⁹Pt α groups in that experiment.

Comments

[†] Using $r_0=1.535$, average of $r_0(^{174}Os)=1.54$ 3, and $r_0(^{176}Os)=1.53$ 4 (1998AkO4).

[‡] For absolute intensity per 100 decays, multiply by 0.0024 3.